

FNK N-Channel Enhancement Mode Power MOSFET

Description

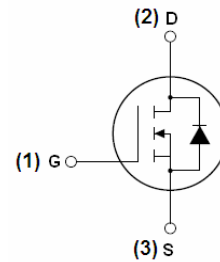
The FNK6585D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

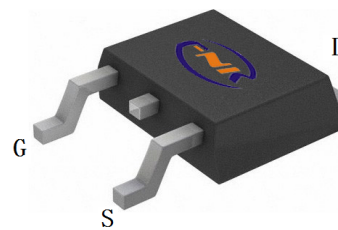
- $V_{DS} = 65V, I_D = 85A$
 $R_{DS(ON)} < 8.6m\Omega @ V_{GS} = 10V$ (Typ: 6.8m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



To-263 Top View

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| FNK6585D | FNK6585D | TO-263 | - | - | - |

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|----------------------|------------|---------------|
| Drain-Source Voltage | V_{DS} | 65 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 85 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_{D(100^\circ C)}$ | 62 | A |
| Pulsed Drain Current | I_{DM} | 340 | A |
| Maximum Power Dissipation | P_D | 160 | W |
| Derating factor | | 1.1 | W/ $^\circ C$ |
| Single pulse avalanche energy ^(Note 5) | E_{AS} | 172 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ C$ |

Thermal Characteristic

| | | | |
|--|-----------------|-----|------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 0.9 | °C/W |
|--|-----------------|-----|------|

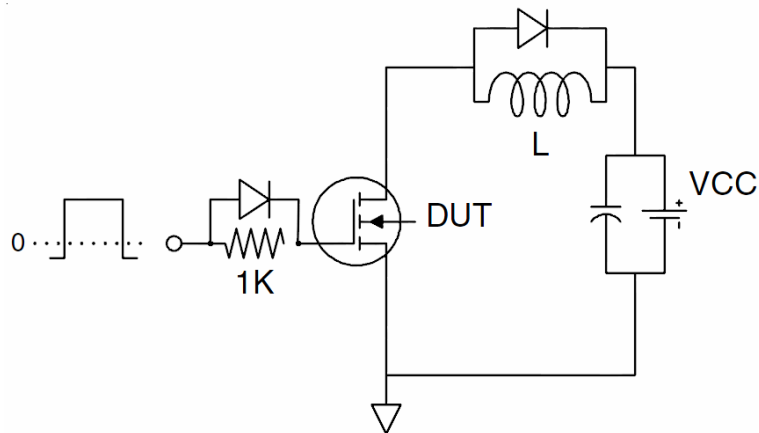
Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|--|--------------|---|-----|------|-----------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | B_{VDSS} | $V_{GS}=0V, I_D=250\mu A$ | 65 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=65V, V_{GS}=0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA |
| On Characteristics ^(Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2 | 2.9 | 4 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=30A$ | - | 6.8 | 8.6 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=10V, I_D=100A$ | 25 | - | - | S |
| Dynamic Characteristics ^(Note 4) | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$ | - | 3225 | - | PF |
| Output Capacitance | C_{oss} | | - | 360 | - | PF |
| Reverse Transfer Capacitance | C_{rss} | | - | 285 | - | PF |
| Switching Characteristics ^(Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=30V, I_D=2A, R_L=15\Omega$ $V_{GS}=10V, R_G=2.5\Omega$ | - | 15 | - | nS |
| Turn-on Rise Time | t_r | | - | 11 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 52 | - | nS |
| Turn-Off Fall Time | t_f | | - | 13 | - | nS |
| Total Gate Charge | Q_g | $V_{DS}=30V, I_D=30A,$ $V_{GS}=10V$ | - | 94 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 16 | - | nC |
| Gate-Drain Charge | Q_{gd} | | - | 24 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage ^(Note 3) | V_{SD} | $V_{GS}=0V, I_S=90A$ | - | - | 1.2 | V |
| Diode Forward Current ^(Note 2) | I_S | | - | - | 90 | A |
| Reverse Recovery Time | t_{rr} | $T_J = 25^\circ\text{C}, I_F = 90A$ $di/dt = 100A/\mu\text{s}$ ^(Note 3) | - | 33 | | nS |
| Reverse Recovery Charge | Q_{rr} | | - | 54 | | nC |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ\text{C}, V_{DD}=35V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit
1) EAS test Circuit

2) Gate charge test Circuit

3) Switch Time Test Circuit


Typical Electrical and Thermal Characteristics (Curves)

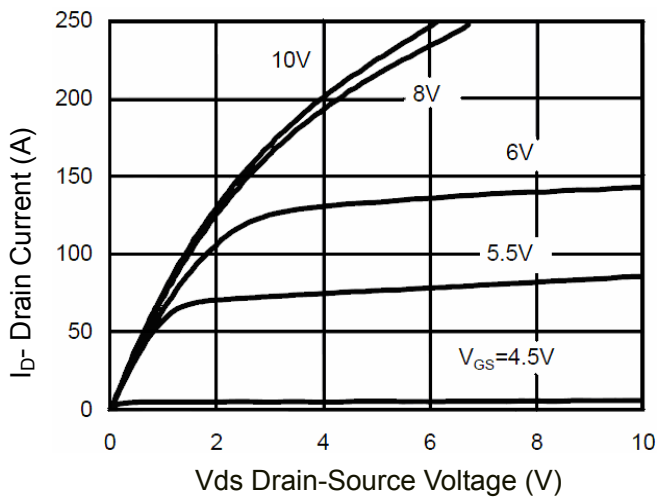


Figure 1 Output Characteristics

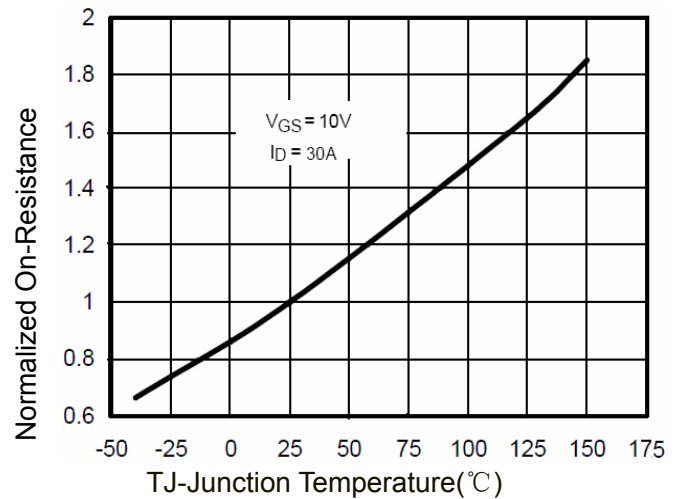


Figure 4 Rdson-Junction Temperature

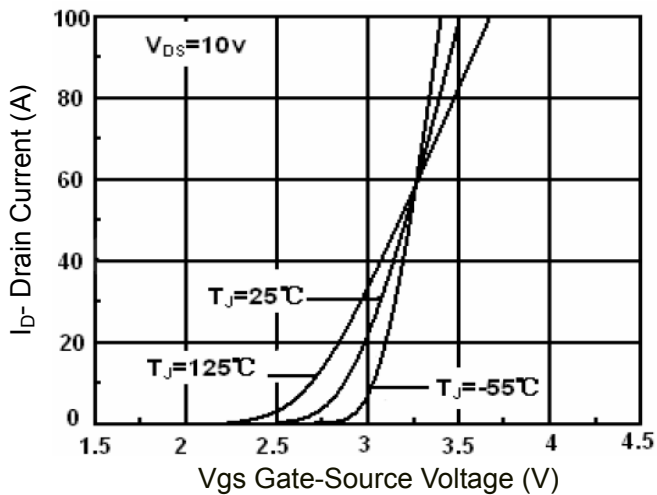


Figure 2 Transfer Characteristics

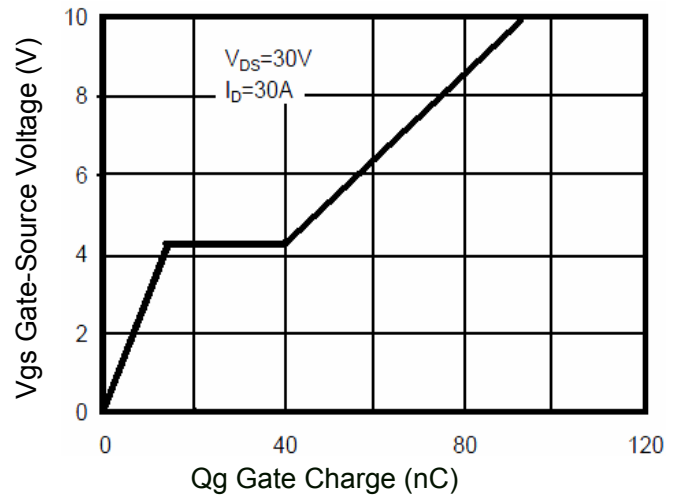


Figure 5 Gate Charge

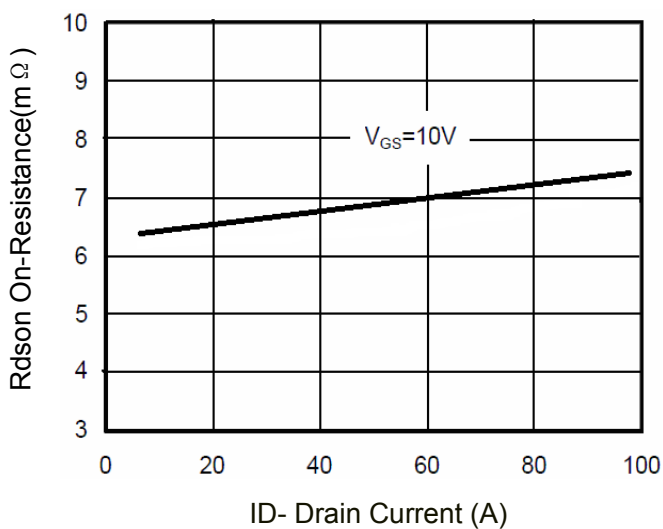


Figure 3 Rdson- Drain Current

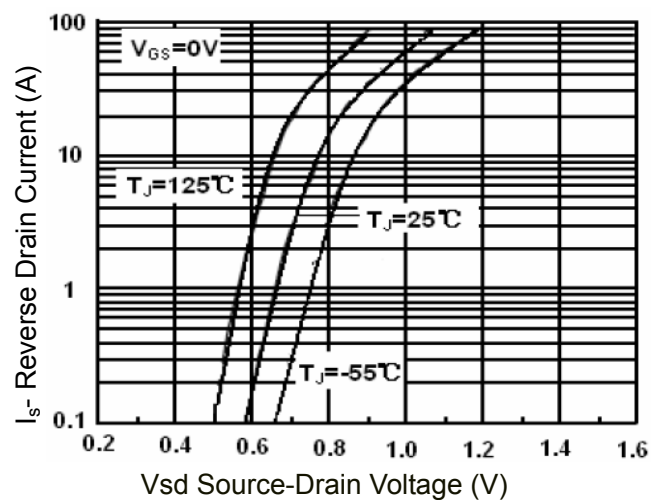


Figure 6 Source- Drain Diode Forward

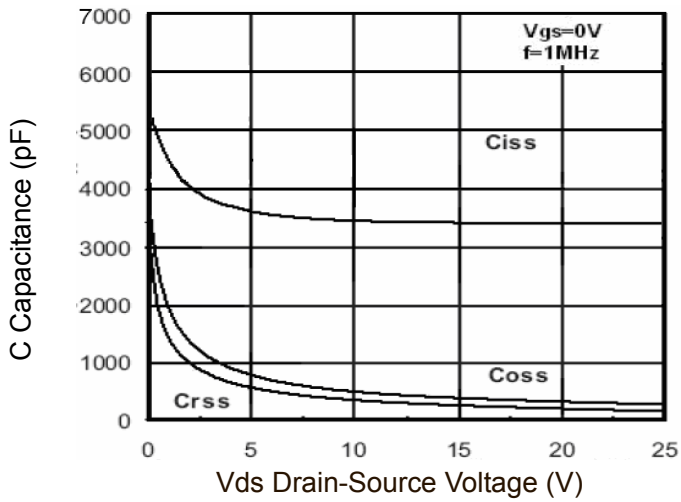


Figure 7 Capacitance vs Vds

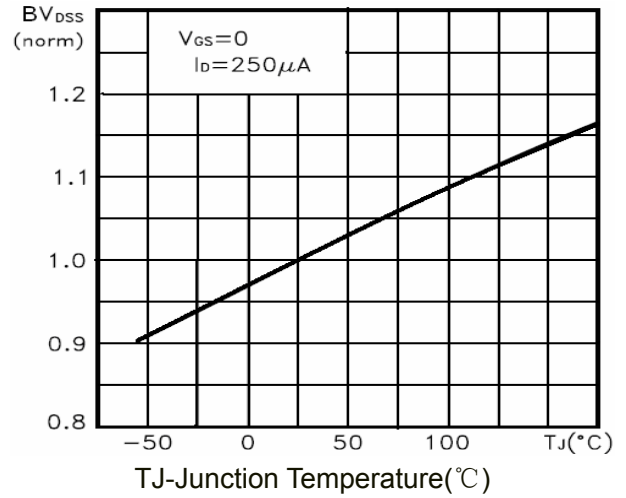


Figure 9 BV_{DSS} vs Junction Temperature

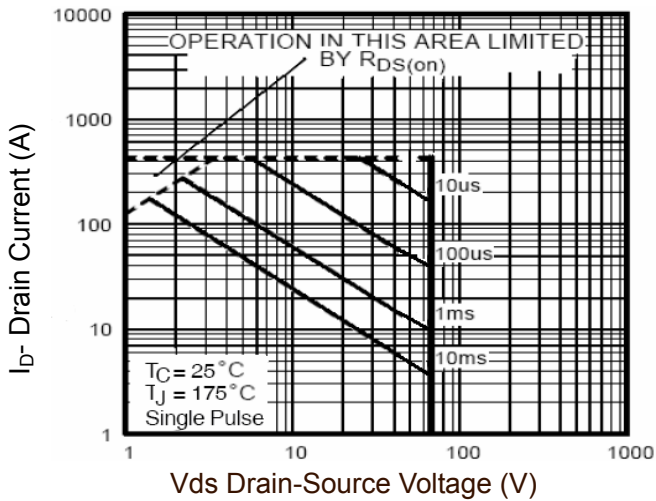


Figure 8 Safe Operation Area

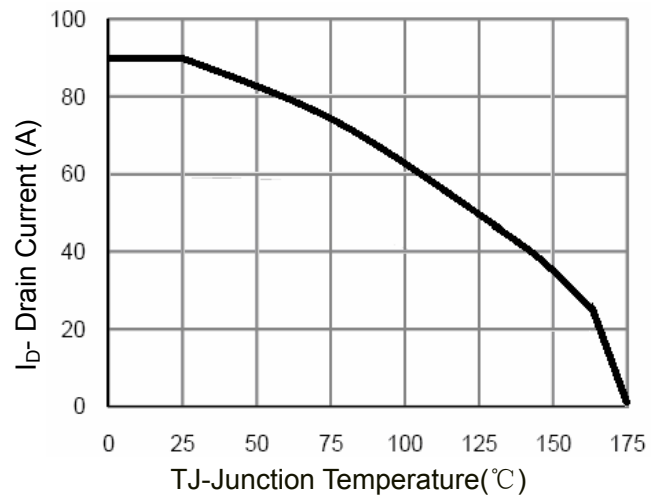


Figure 10 Current vs Junction Temperature

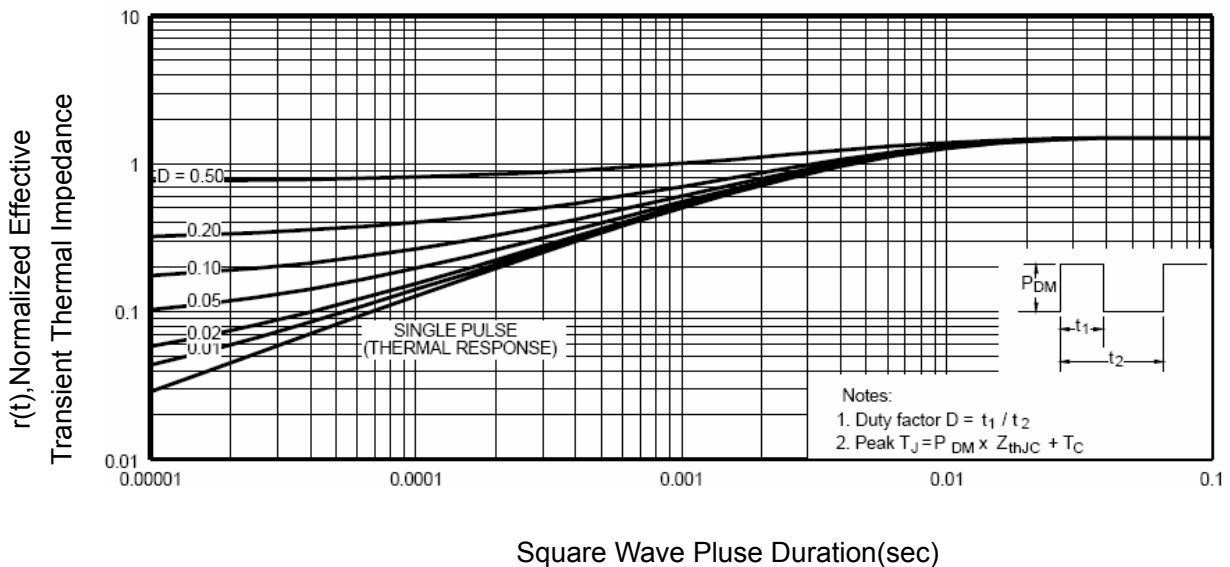
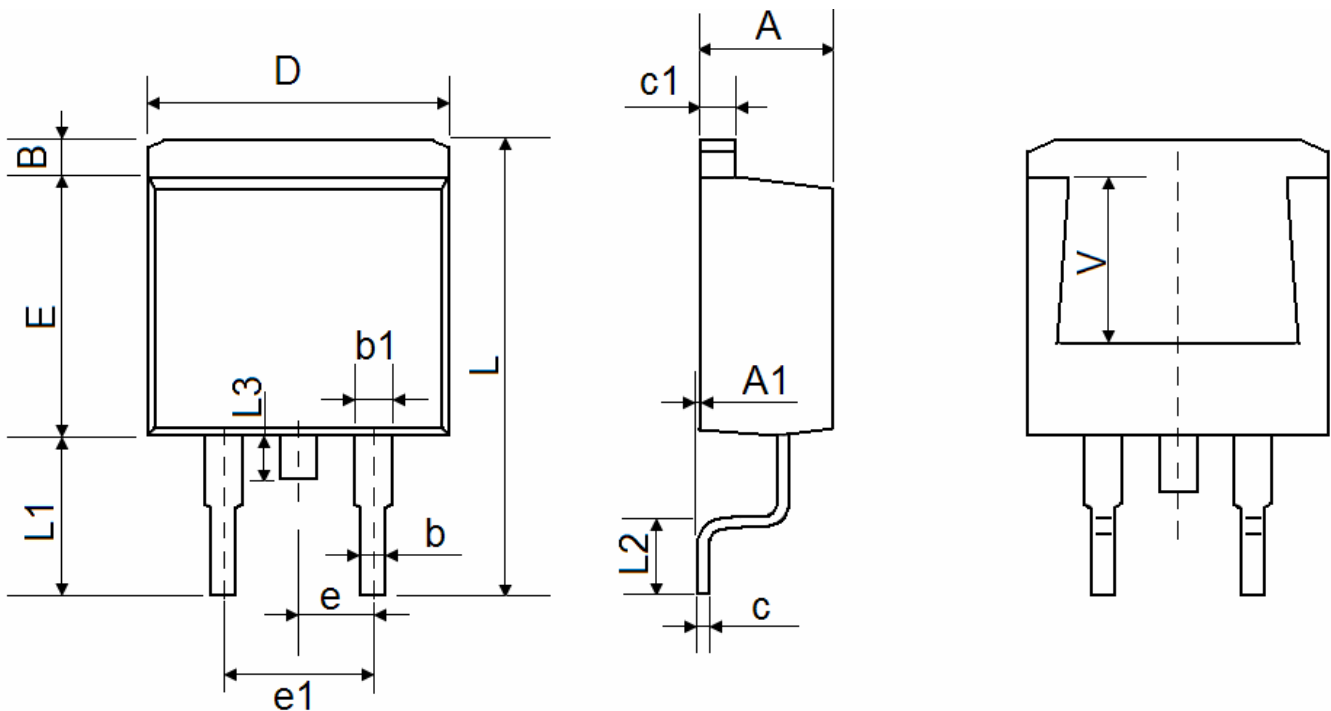


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263 Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.470 | 4.670 | 0.176 | 0.184 |
| A1 | 0.000 | 0.150 | 0.000 | 0.006 |
| B | 1.170 | 1.370 | 0.046 | 0.054 |
| b | 0.710 | 0.910 | 0.028 | 0.036 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 |
| c | 0.310 | 0.530 | 0.012 | 0.021 |
| c1 | 1.170 | 1.370 | 0.046 | 0.054 |
| D | 10.010 | 10.310 | 0.394 | 0.406 |
| E | 8.500 | 8.900 | 0.335 | 0.350 |
| e | 2.540 TYP. | | 0.100 TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| L | 15.050 | 15.450 | 0.593 | 0.608 |
| L1 | 5.080 | 5.480 | 0.200 | 0.216 |
| L2 | 2.340 | 2.740 | 0.092 | 0.108 |
| L3 | 1.300 | 1.700 | 0.051 | 0.067 |
| V | 5.600 REF | | 0.220 REF | |

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